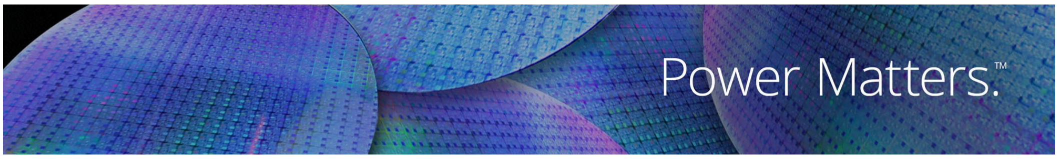
POWER DISCRETES & MODULES

- Voltage & Current Regulation Diodes
- Small Signal Diodes and Diode Arrays
- IGBT
- Power MOSFET
- Silicon Carbide (SiC) Semiconductor
- Power Modules
- JFET
- BJT (BiPolar Junction Transistor)
  - BJT Modules (Power Integrated Circuit, PIC)
  - Darlington Transistors
  - Darlington Transistor Array
  - NPN PNP Complimentary Transistor
  - NPN Transistor
  - PNP Transistor
- Legacy Power Discretes & Modules
- Diode and Rectifier Devices



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JAN2N2481 (#19796)

Product Status

In Production

Overview Resources Diagrams Ordering Support

Package Carrier:	ESD Bag

Electrical Rating	Symbol	Min	Typ	Max	Unit
DC Current Gain	HFE	40		120	
Turn Off Time (nS)	t_{off}			45	ns

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	I_C			0.01	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			15	V
Junction Temperature (°C)	T_J			200	°C

Alphanumeric Parameter	Value
Quality Level	JAN

This part can be found in the following product categories:

- Power Discretes & Modules ▸ BJT (BiPolar Junction Transistor) ▸ NPN Transistor
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